

Form PTO-1449 (Rev. 8-83)	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 0756-1880	Serial No. New Application- 09/188 382
INFORMATION DISCLOSURE STATEMENT CORRECTED FORM <i>(Use several sheets if necessary)</i>		Applicant: Takashi INUSHIMA et al	
		Filing Date: November 10, 1998	Group: 1762
OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)			
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Examiner <i>Panaito</i>	Date Considered 12-9-99		

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